ΡΛΝ	ĴΪΤ
	SEMI CONDUCTOR

60V N-Channel Enhancement Mode MOSFET

Current

Voltage

48 A

Features

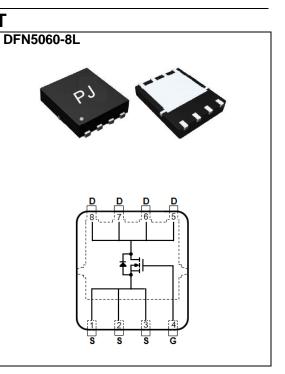
• $R_{DS(ON)}$, $V_{GS}@10V$, $I_D@20A<17m\Omega$

60 V

- R_{DS(ON)}, V_{GS}@4.5V, I_D@10A<20mΩ
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case: DFN5060-8L Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0028 ounces, 0.08 grams



Maximum Ratings and Thermal Characteristics ($T_A=25^{\circ}C$ unless otherwise noted)

PARAME	TED	SYMBOL	LIMIT	UNITS	
		STNIBOL		UNITS	
Drain-Source Voltage		V _{DS}	60	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	v	
Continuous Drain Current	T _C =25°C		48	A	
	T _C =100°C	Ι _D	30		
Pulsed Drain Current (Note 1)	T _c =25°C	I _{DM}	192		
Power Dissipation	T _c =25°C	D	83	W	
	T _c =100°C	PD	33		
Continuous Drain Current	T _A =25°C	Ι _D	7.4	A	
	T _A =70°C		6.0		
Power Dissipation	T _A =25°C	Po	2.0	W	
	T _A =70°C		1.3		
Single Pulse Avalanche Energy (Note 6)		E _{AS}	45	mJ	
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~150	°C	
Typical Thermal Resistance ^(Note 4,5)	5) Junction to Case	$R_{ extsf{ heta}JC}$	1.5	°C/W	
	Junction to Ambient	R _{θJA}	62.5		
 Limited only By Maximum J 	unction Temperature				



Electrical Characteristics ($T_A=25^{\circ}C$ unless otherwise noted)

		TEAT CONDITION		TVD		
PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static	1	Γ	Г	1		1
Drain-Source Breakdown Voltage	BV _{DSS}	V_{GS} =0V, I _D =250uA	60	-	-	V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250$ uA	1.0	1.7	2.5	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =20A	-	13	17	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =4.5V, I _D =10A	-	15	20	mΩ
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =60V, V_{GS} =0V	-	-	1.0	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V, V _{DS} =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 7)		·				
Total Gate Charge	Qg	V_{DS} =30V, I _D =10A, V _{GS} =4.5V ^(Note 1,2)	-	13.5	-	
Gate-Source Charge	Q _{gs}		-	4.8	-	nC
Gate-Drain Charge	Q _{gd}		-	4.9	-	
Input Capacitance	Ciss	V _{DS} =25V, V _{GS} =0V, f=1.0MHZ	-	1574	-	
Output Capacitance	Coss		-	118	-	pF
Reverse Transfer Capacitance	Crss		-	77	-	
Turn-On Delay Time	td _(on)	$V_{DD}=15V, I_{D}=1A,$ $V_{GS}=10V, R_{G}=6\Omega$ (Note 1,2)	-	11	-	
Turn-On Rise Time	tr		-	11	-	-
Turn-Off Delay Time	td _(off)		-	35	-	ns
Turn-Off Fall Time	t _f		-	8.1	-	
Drain-Source Diode						
Maximum Continuous Drain-Source					10	•
Diode Forward Current	I _S		-	-	48	A
Diode Forward Voltage	V _{SD}	I _S =1A, V _{GS} =0V	-	0.68	1	V

NOTES :

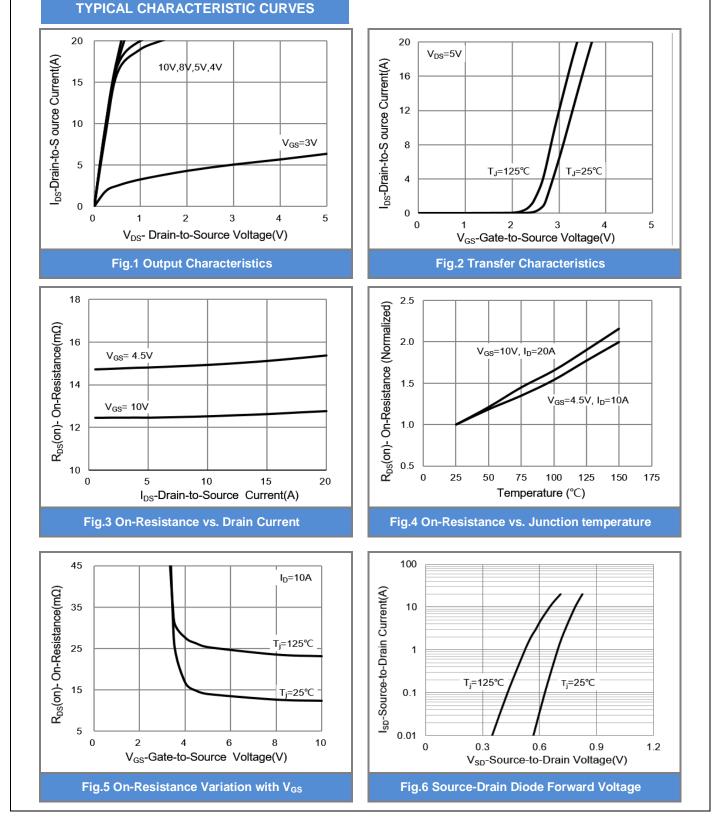
1. Pulse width<u><</u>300us, Duty cycle<u><</u>2%

2. Essentially independent of operating temperature typical characteristics.

 Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.

- 4. The maximum current rating is package limited.
- 5. R_{0JA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH, I_{AS} =30A, V_{DD} =25V, V_{GS} =10V, Starting T_J=25°C
- 7. Guaranteed by design, not subject to production testing.

March 27,2018-REV.01

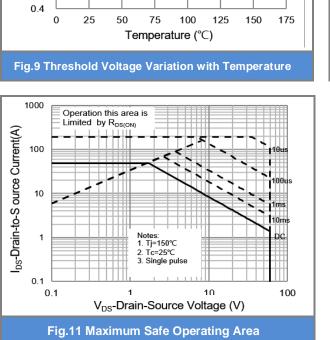


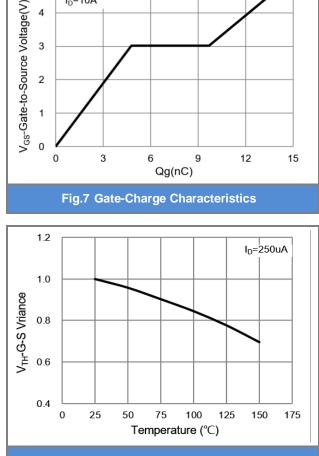
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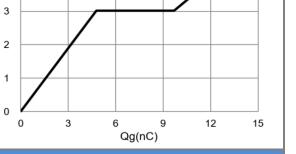
Page 3

March 27,2018-REV.01

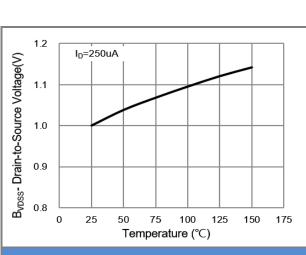








TYPICAL CHARACTERISTIC CURVES





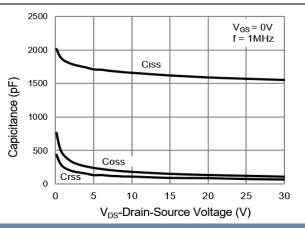


Fig.10 Capacitance vs. Drain-Source Voltage





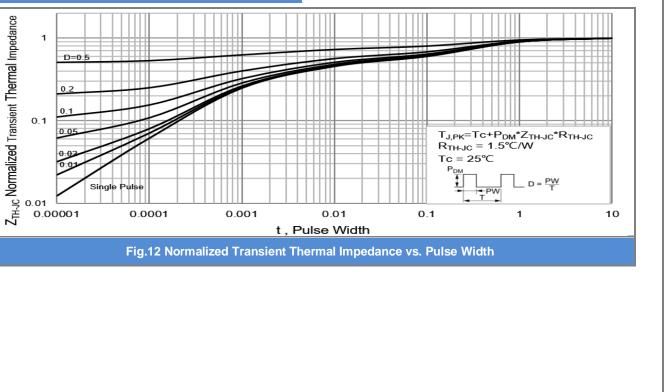
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V_{DS}=30V I_D=10A







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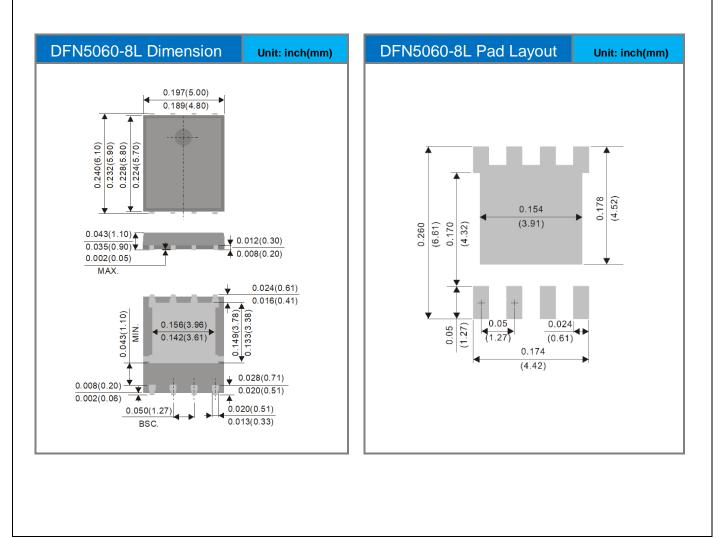
TYPICAL CHARACTERISTIC CURVES



Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJQ5466A1_R2_00001	DFN5060-8L	3000pcs / 13" reel	Q5466A1	Halogen free

Packaging Information & Mounting Pad Layout





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